



20 μ A Maximum, Rail-to-Rail I/O, Zero Input Crossover Distortion Amplifiers

AD8506/AD8508

FEATURES

PSRR: 100 dB minimum

CMRR: 105 dB typical

Very low supply current: 20 μ A per amp maximum

1.8 V to 5 V single-supply or ± 0.9 V to ± 2.5 V dual-supply operation

Rail-to-rail input and output

Low noise: 45 nV/ $\sqrt{\text{Hz}}$ @ 1 kHz

2.5 mV offset voltage maximum

Very low input bias current: 1 pA typical

APPLICATIONS

Pressure and position sensors

Remote security

Bio sensors

IR thermometers

Battery-powered consumer equipment

Hazard detectors

GENERAL DESCRIPTION

The AD8506/AD8508 are dual and quad micropower amplifiers featuring rail-to-rail input and output swings while operating from a 1.8 V to 5 V single or from ± 0.9 V to ± 2.5 V dual power supply.

Using a novel circuit technology, these low cost amplifiers offer zero crossover distortion (excellent PSRR and CMRR performance) and very low bias current, while operating with a supply current of less than 20 μ A per amplifier. This amplifier family offers the lowest noise in its power class.

This combination of features makes the AD8506/AD8508 amplifiers ideal choices for battery-powered applications because they minimize errors due to power supply voltage variations over the lifetime of the battery and maintain high CMRR even for a rail-to-rail input op amp.

PIN CONFIGURATIONS

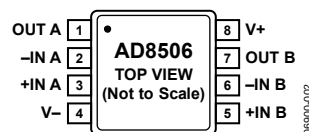


Figure 1. 8-Lead MSOP (RM-8)

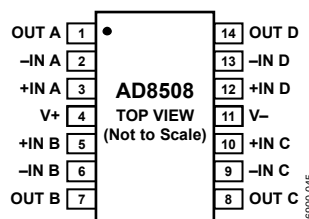


Figure 2. 14-Lead TSSOP (RU-14)

Remote battery-powered sensors, handheld instrumentation and consumer equipment, hazard detection (for example, smoke, fire, and gas), and patient monitors can benefit from the features of the AD8506/AD8508 amplifiers.

The AD8506/AD8508 are specified for both the industrial temperature range of -40°C to $+85^{\circ}\text{C}$ and the extended industrial temperature range of -40°C to $+125^{\circ}\text{C}$. The AD8506 dual amplifiers are available in an 8-lead MSOP package. The AD8508 quad amplifiers are available in the 14-lead TSSOP package.

Rev. A

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REVISION HISTORY

7/08—Rev. 0 to Rev. A

Added AD8508	Universal
Added TSSOP Package	Universal
Changes to Features Section and General Description Section .	1
Added Figure 2; Renumbered Sequentially	1
Changed Electrical Characteristics Heading to Electrical	
Characteristics—5 V Operation	3
Changes to Table 1.....	3
Added Electrical Characteristics—1.8 V Operation Heading....	4
Changes to Table 2.....	4
Changes to Table 3, Thermal Resistance Section, and Table 4 ...	5
Added $T_A = 25^\circ\text{C}$ Condition to Typical Performance	
Characteristics Section.....	6
Changes to Figure 3, Figure 4, Figure 6, and Figure 7	6
Added Figure 11 and Figure 14.....	7

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Added Figure 39 and Figure 40	12
Added Theory of Operation Section, Figure 41, and	
Figure 42	13
Added Figure 43 and Figure 44	14
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11/07—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—5 V OPERATION

$V_{SY} = 5\text{ V}$, $V_{CM} = V_{SY}/2$, $T_A = 25^\circ\text{C}$, $R_L = 100\text{ k}\Omega$ to GND, unless otherwise noted.

Table 1.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V _{OS}	0 V ≤ V _{CM} ≤ 5 V −40°C ≤ T _A ≤ +125°C		0.5	2.5	mV
Input Bias Current	I _B			1	3.5	mV
		−40°C ≤ T _A ≤ +85°C			10	pA
		−40°C ≤ T _A ≤ +125°C			100	pA
Input Offset Current	I _{OS}			0.5	600	pA
		−40°C ≤ T _A ≤ +85°C			5	pA
		−40°C ≤ T _A ≤ +125°C			50	pA
Input Voltage Range		−40°C ≤ T _A ≤ +125°C	0		130	pA
Common-Mode Rejection Ratio	CMRR	0 V ≤ V _{CM} ≤ 5 V	90	105	5	V
		−40°C ≤ T _A ≤ +85°C	90			dB
		−40°C ≤ T _A ≤ +125°C	85			dB
Large Signal Voltage Gain	A _{VO}	0.05 V ≤ V _{OUT} ≤ 4.95 V	105	120		dB
		−40°C ≤ T _A ≤ +125°C	100			dB
		−40°C ≤ T _A ≤ +125°C		2		μV/°C
Offset Voltage Drift	ΔV _{OS} /ΔT	−40°C ≤ T _A ≤ +125°C				
Input Capacitance Differential Mode	C _{DIFF}			3		pF
Input Capacitance Common Mode	C _{CM}			4.2		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	R _L = 100 kΩ to GND	4.98	4.99		V
		−40°C ≤ T _A ≤ +125°C	4.98			V
		R _L = 10 kΩ to GND	4.9	4.95		V
		−40°C ≤ T _A ≤ +125°C	4.9			V
Output Voltage Low	V _{OL}	R _L = 100 kΩ to V _{SY}		2	5	mV
		−40°C ≤ T _A ≤ +125°C			5	mV
		R _L = 10 kΩ to V _{SY}		10	25	mV
		−40°C ≤ T _A ≤ +125°C			30	mV
Short-Circuit Limit	I _{SC}	V _{OUT} = V _{SY} or GND		±45		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	V _{SY} = 1.8 V to 5 V	100	110		dB
		−40°C ≤ T _A ≤ +85°C	100			dB
		−40°C ≤ T _A ≤ +125°C	95			dB
Supply Current per Amplifier	I _{SY}	V _{OUT} = V _{SY} /2		15	20	μA
		−40°C ≤ T _A ≤ +125°C			25	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	R _L = 100 kΩ, C _L = 10 pF, G = 1		13		mV/μs
Gain Bandwidth Product	GBP	R _L = 1 MΩ, C _L = 20 pF, G = 1		95		kHz
Phase Margin	Φ _M	R _L = 1 MΩ, C _L = 20 pF, G = 1		60		Degrees
NOISE PERFORMANCE						
Voltage Noise	e _n p-p	f = 0.1 Hz to 10 Hz		2.8		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		45		nV/√Hz
Current Noise Density	i _n	f = 1 kHz		15		fA/√Hz

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ELECTRICAL CHARACTERISTICS—1.8 V OPERATION

$V_{SY} = 1.8 \text{ V}$, $V_{CM} = V_{SY}/2$, $T_A = 25^\circ\text{C}$, $R_L = 100 \text{ k}\Omega$ to GND, unless otherwise noted.

Table 2.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
INPUT CHARACTERISTICS							
Offset Voltage	V _{OS}	0 V ≤ V _{CM} ≤ 1.8 V −40°C ≤ T _A ≤ +125°C		0.5	2.5	mV	
Input Bias Current	I _B	−40°C ≤ T _A ≤ +85°C −40°C ≤ T _A ≤ +125°C		1	3.5	mV	
					10	pA	
					100	pA	
Input Offset Current	I _{OS}	−40°C ≤ T _A ≤ +85°C −40°C ≤ T _A ≤ +125°C		0.5	600	pA	
					5	pA	
					50	pA	
Input Voltage Range	CMRR	−40°C ≤ T _A ≤ +125°C	0		100	pA	
−40°C ≤ T _A ≤ +125°C		1.8			V		
Common-Mode Rejection Ratio		0 V ≤ V _{CM} ≤ 1.8 V			85	100	dB
Large Signal Voltage Gain	A _{VO}	−40°C ≤ T _A ≤ +85°C	85			dB	
		−40°C ≤ T _A ≤ +125°C				80	dB
		0.05 V ≤ V _{OUT} ≤ 1.75 V				95	115
Offset Voltage Drift	ΔV _{OS} /ΔT	−40°C ≤ T _A ≤ +125°C				dB	
Input Capacitance Differential Mode	C _{DIFF}			2.5		μV/°C	
Input Capacitance Common Mode	C _{CM}			3		pF	
				4.2		pF	
OUTPUT CHARACTERISTICS							
Output Voltage High	V _{OH}	R _L = 100 kΩ to GND −40°C ≤ T _A ≤ +125°C	1.78	1.79		V	
Output Voltage Low	V _{OL}	R _L = 10 kΩ to GND −40°C ≤ T _A ≤ +125°C	1.78			V	
		R _L = 10 kΩ to GND −40°C ≤ T _A ≤ +125°C	1.65	1.75		V	
		R _L = 100 kΩ to V _{SY} −40°C ≤ T _A ≤ +125°C	1.65			V	
		R _L = 100 kΩ to V _{SY} −40°C ≤ T _A ≤ +125°C		2	5	mV	
		R _L = 10 kΩ to V _{SY} −40°C ≤ T _A ≤ +125°C			5	mV	
		R _L = 10 kΩ to V _{SY} −40°C ≤ T _A ≤ +125°C		12	25	mV	
Short-Circuit Limit	I _{SC}	V _{OUT} = V _{SY} or GND			25	mV	
				±4.5		mA	
POWER SUPPLY							
Power Supply Rejection Ratio	PSRR	V _{SY} = 1.8 V to 5 V −40°C ≤ T _A ≤ +85°C −40°C ≤ T _A ≤ +125°C	100	110		dB	
Supply Current per Amplifier	I _{SY}	V _{OUT} = V _{SY} /2	100			dB	
		−40°C ≤ T _A ≤ +125°C	95			dB	
				16.5	20	μA	
					25	μA	
DYNAMIC PERFORMANCE							
Slew Rate	SR	R _L = 100 kΩ, C _L = 10 pF, G = 1		13		mV/μs	
Gain Bandwidth Product	GBP	R _L = 1 MΩ, C _L = 20 pF, G = 1		95		kHz	
Phase Margin	Φ _M	R _L = 1 MΩ, C _L = 20 pF, G = 1		60		Degrees	
NOISE PERFORMANCE							
Voltage Noise	e _n p-p	f = 0.1 Hz to 10 Hz		2.8		μV p-p	
Voltage Noise Density	e _n	f = 1 kHz		45		nV/√Hz	
Current Noise Density	i _n	f = 1 kHz		15		fA/√Hz	

ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
Supply Voltage	5.5 V
Input Voltage	$\pm V_{SY} \pm 0.1$ V
Input Current ¹	± 10 mA
Differential Input Voltage ²	$\pm V_{SY}$
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	–65°C to +150°C
Operating Temperature Range	–40°C to +125°C
Junction Temperature Range	–65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C

¹ Input pins have clamp diodes to the supply pins. Input current should be limited to 10 mA or less whenever the input signal exceeds the power supply rail by 0.5 V.

² Differential input voltage is limited to 5 V or the supply voltage, whichever is less.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages. This was measured using a standard two-layer board.

Table 4. Thermal Resistance

Package Type	θ_{JA}	θ_{JC}	Unit
8-Lead MSOP (RM-8)	190	44	°C/W
14-Lead TSSOP (RU-14)	180	35	°C/W

ESD CAUTION



ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

TYPICAL PERFORMANCE CHARACTERISTICS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

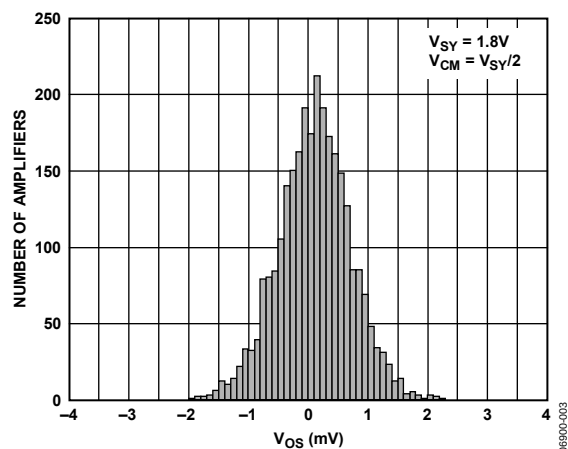


Figure 3. Input Offset Voltage Distribution

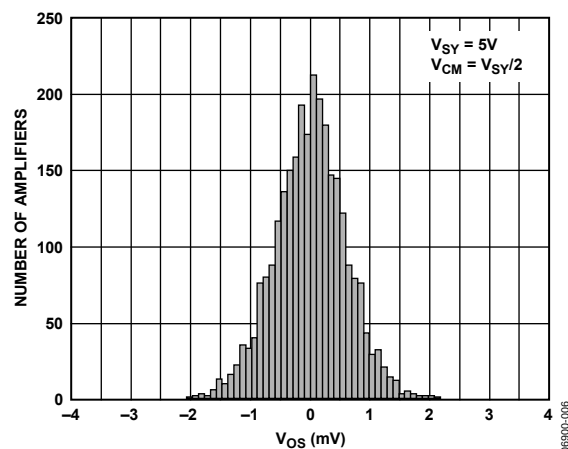


Figure 6. Input Offset Voltage Distribution

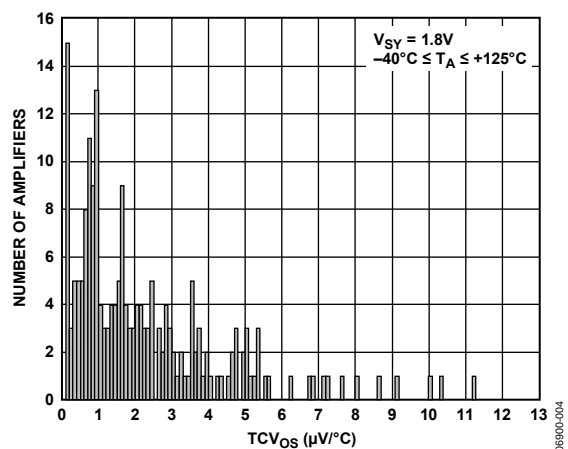


Figure 4. Input Offset Voltage Drift Distribution

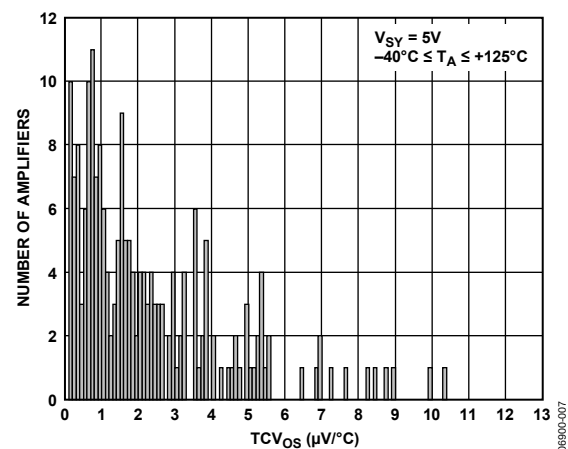


Figure 7. Input Offset Voltage Drift Distribution

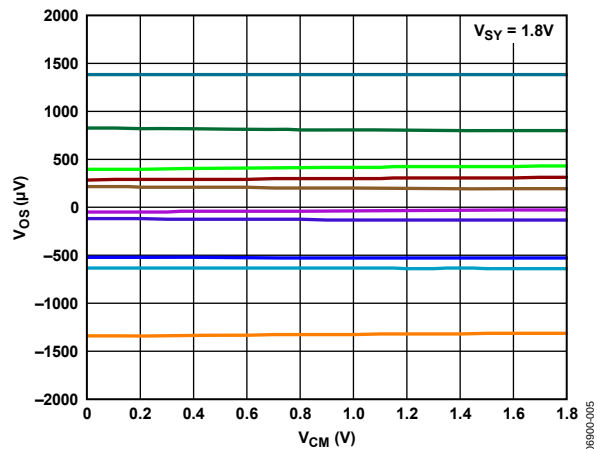


Figure 5. Input Offset Voltage vs. Input Common-Mode Voltage

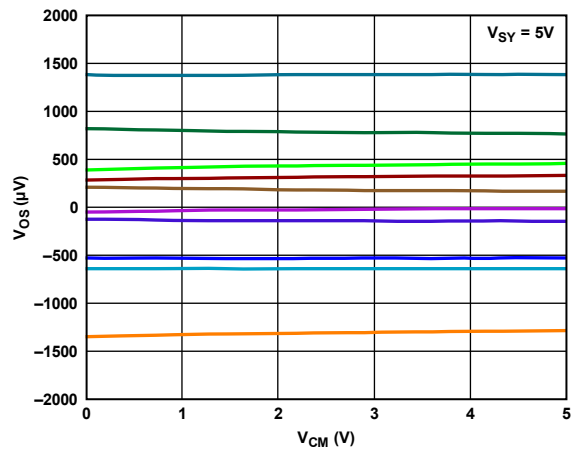


Figure 8. Input Offset Voltage vs. Input Common-Mode Voltage

$T_A = 25^\circ\text{C}$, unless otherwise noted.

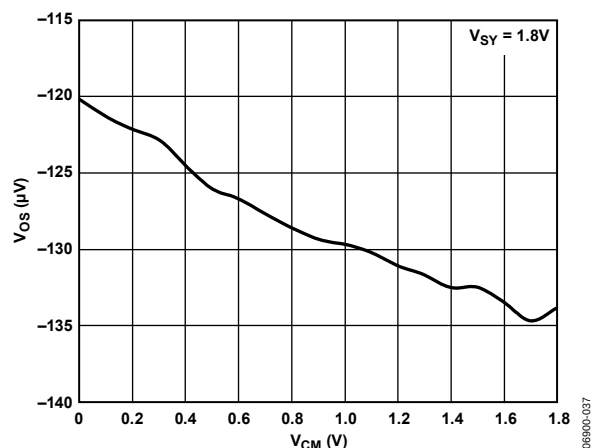


Figure 9. Input Offset Voltage vs. Input Common-Mode Voltage

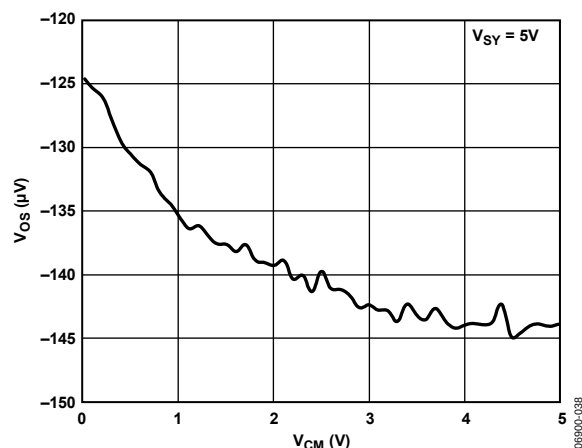


Figure 12. Input Offset Voltage vs. Input Common-Mode Voltage

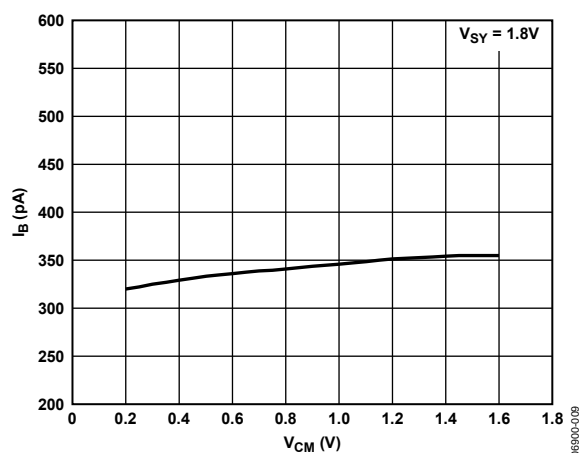


Figure 10. Input Bias Current vs. Common-Mode Voltage at 125°C

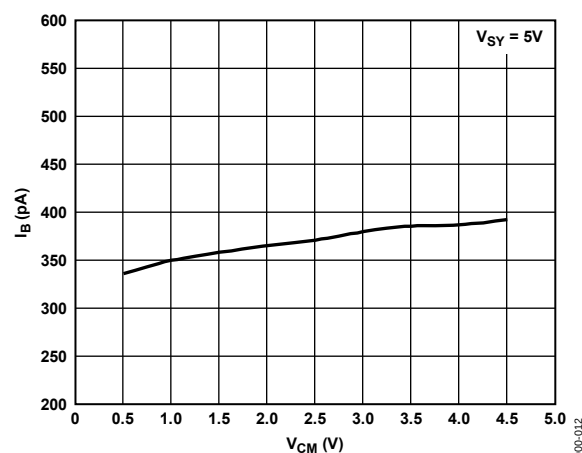


Figure 13. Input Bias Current vs. Common-Mode Voltage at 125°C

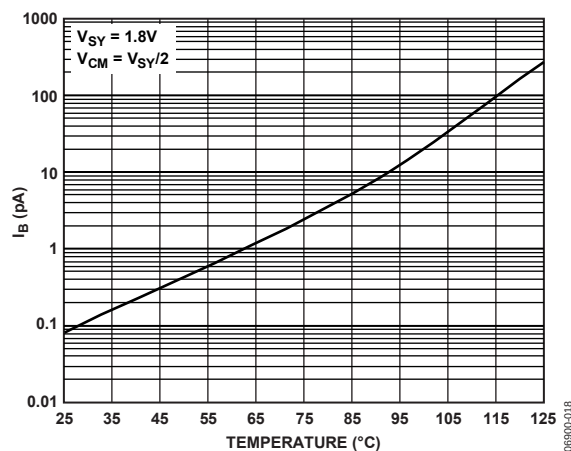


Figure 11. Input Bias Current vs. Temperature

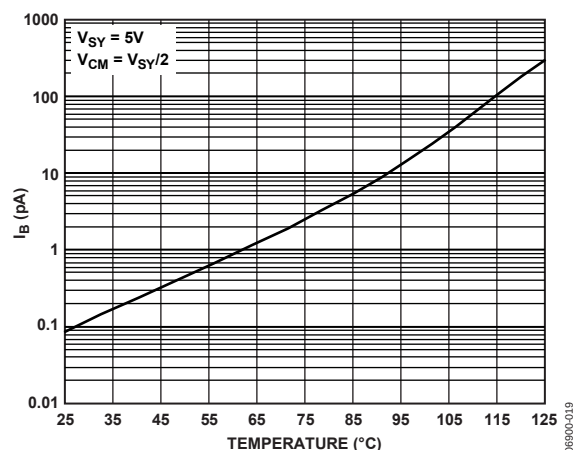


Figure 14. Input Bias Current vs. Temperature

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$T_A = 25^\circ\text{C}$, unless otherwise noted.

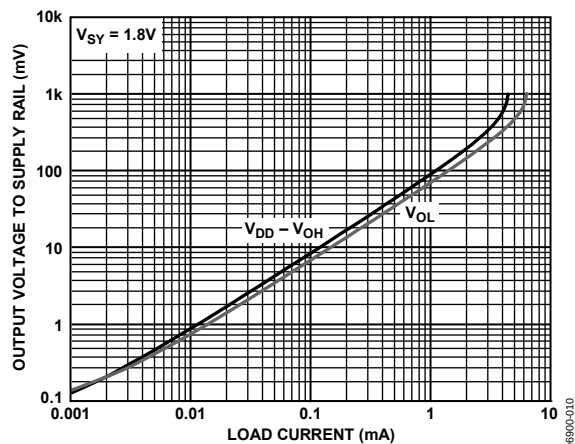


Figure 15. Output Voltage to Supply Rail vs. Load Current

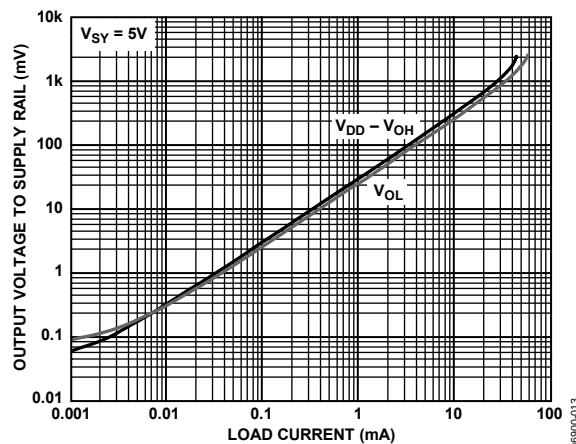


Figure 18. Output Voltage to Supply Rail vs. Load Current

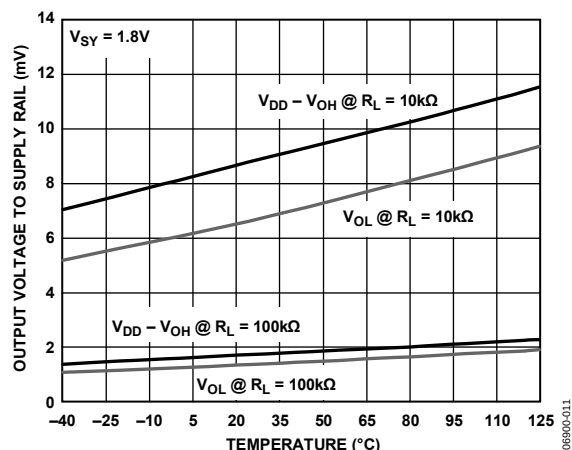


Figure 16. Output Voltage to Supply Rail vs. Temperature

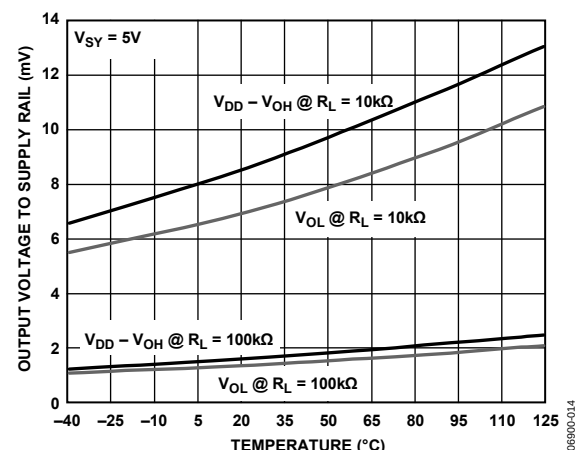


Figure 19. Output Voltage to Supply Rail vs. Temperature

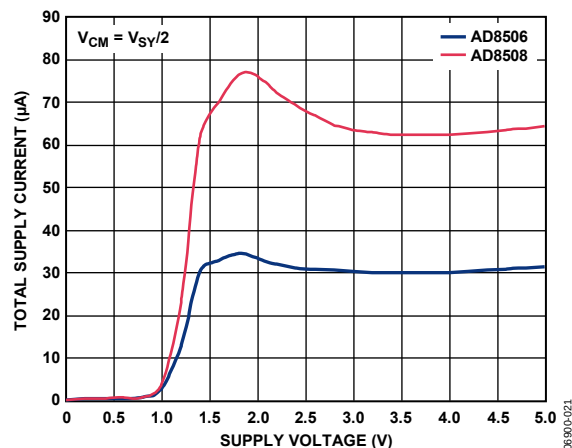


Figure 17. Total Supply Current vs. Supply Voltage

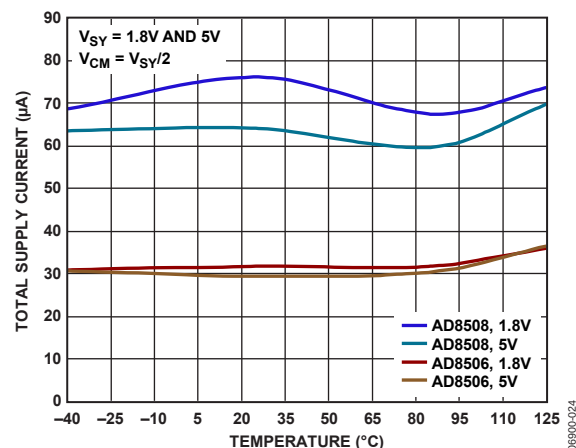


Figure 20. Total Supply Current vs. Temperature

$T_A = 25^\circ\text{C}$, unless otherwise noted.

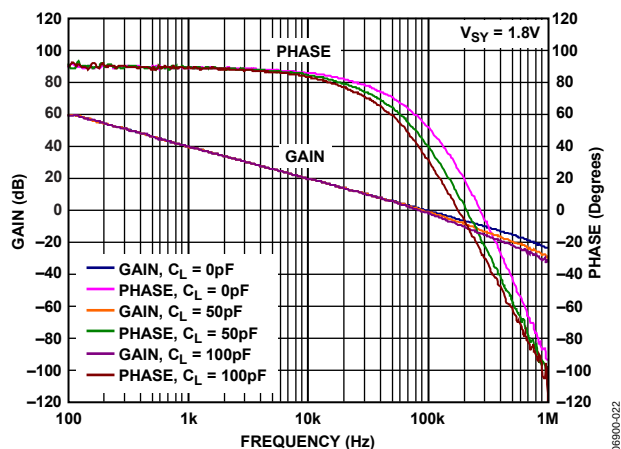


Figure 21. Open-Loop Gain and Phase vs. Frequency

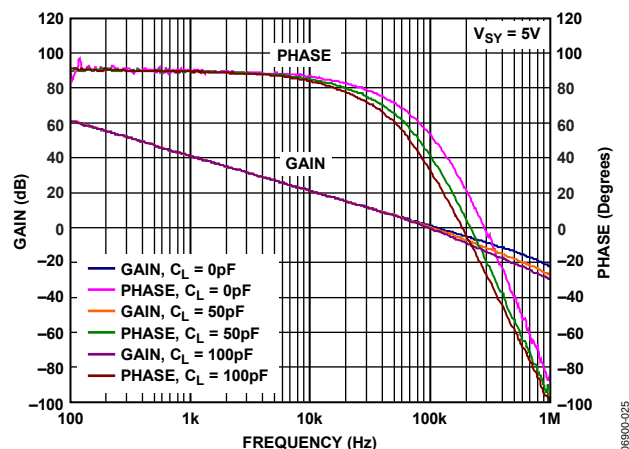


Figure 24. Open-Loop Gain and Phase vs. Frequency

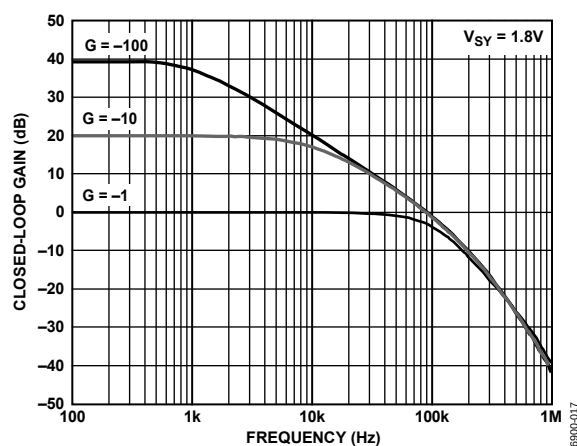


Figure 22. Closed-Loop Gain vs. Frequency

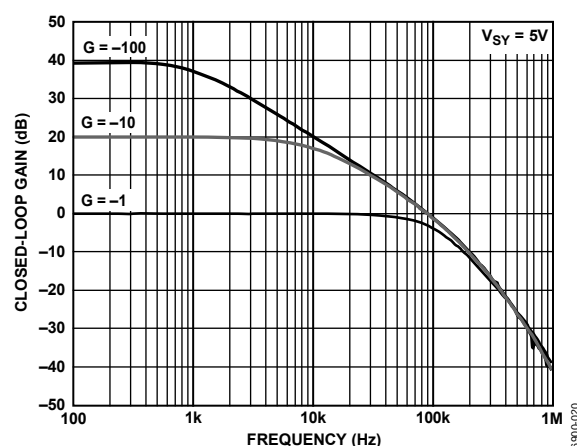


Figure 25. Closed-Loop Gain vs. Frequency

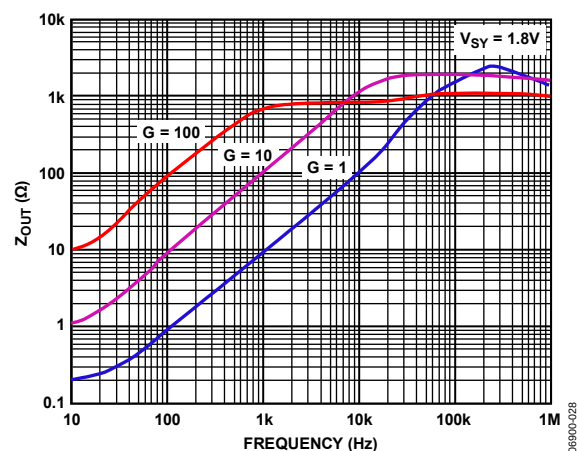


Figure 23. Z_{OUT} vs. Frequency

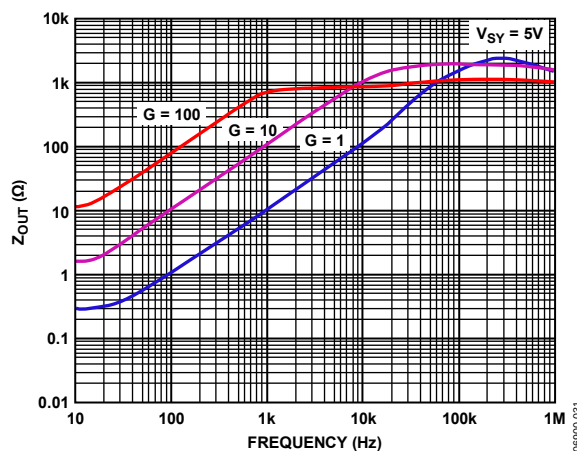


Figure 26. Z_{OUT} vs. Frequency

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$T_A = 25^\circ\text{C}$, unless otherwise noted.

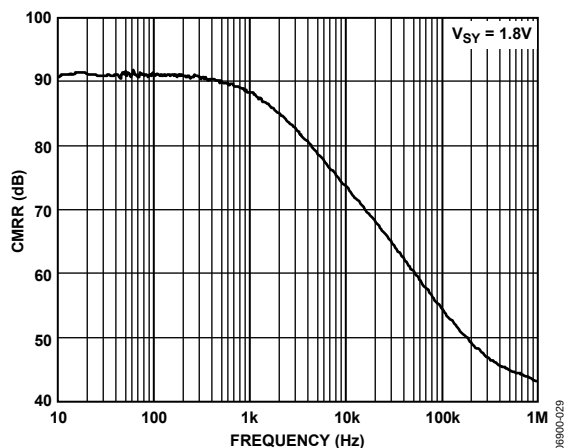


Figure 27. CMRR vs. Frequency

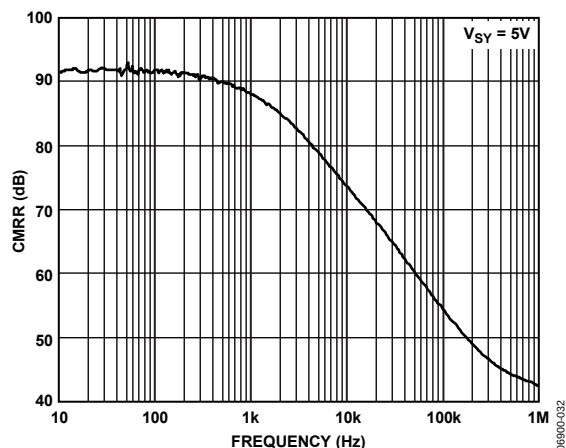


Figure 30. CMRR vs. Frequency

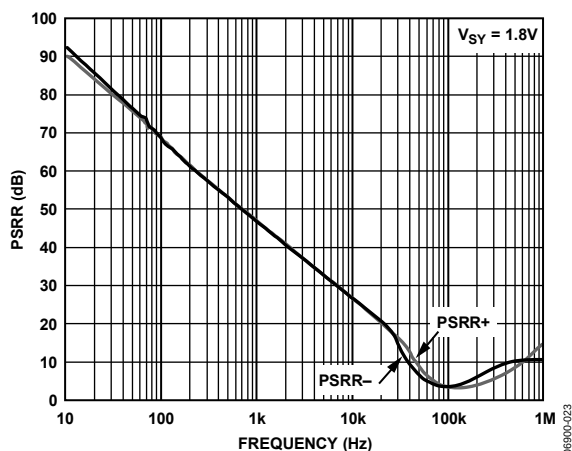


Figure 28. PSRR vs. Frequency

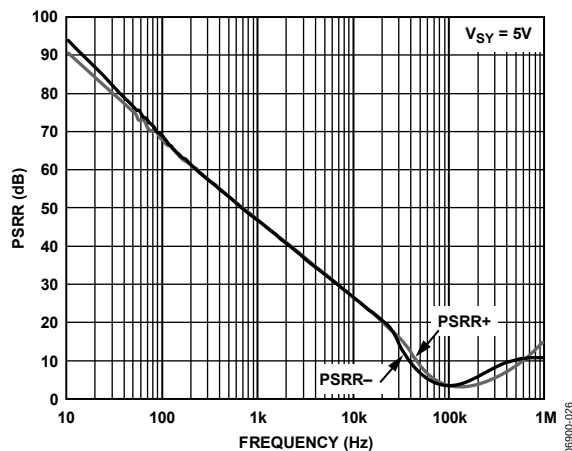


Figure 31. PSRR vs. Frequency

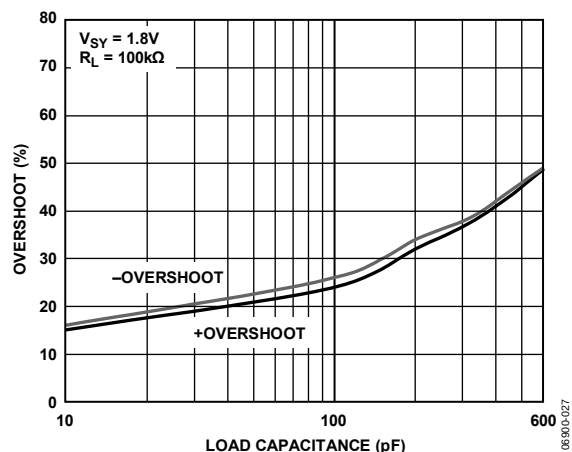


Figure 29. Small Signal Overshoot vs. Load Capacitance

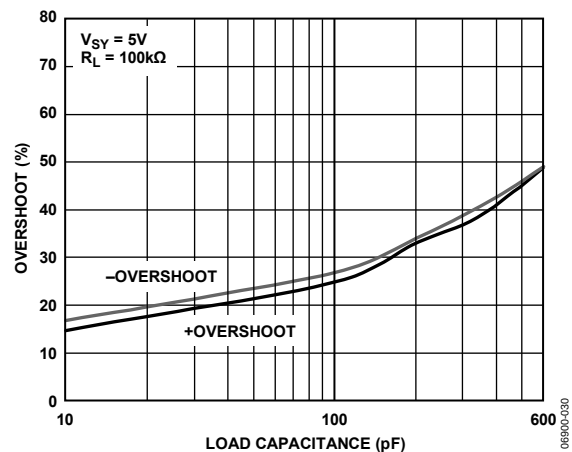


Figure 32. Small Signal Overshoot vs. Load Capacitance

$T_A = 25^\circ\text{C}$, unless otherwise noted.

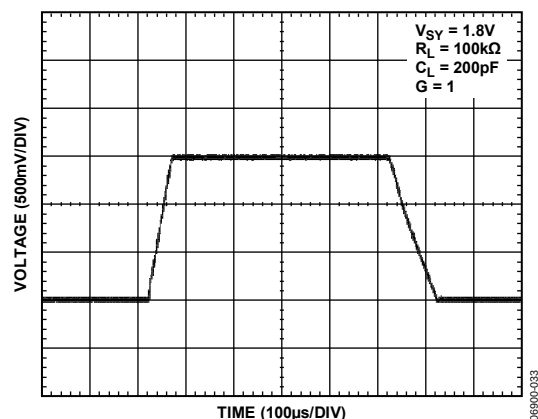


Figure 33. Large Signal Transient Response

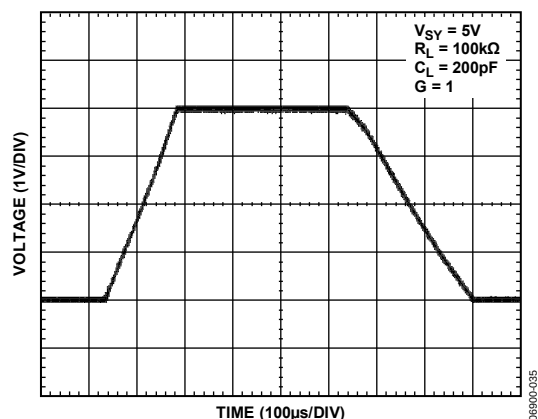


Figure 36. Large Signal Transient Response

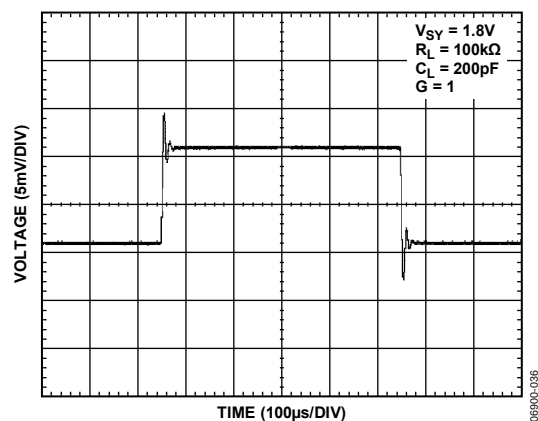


Figure 34. Small Signal Transient Response

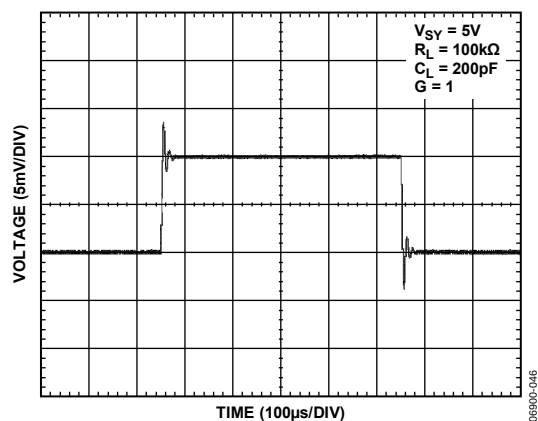


Figure 37. Small Signal Transient Response

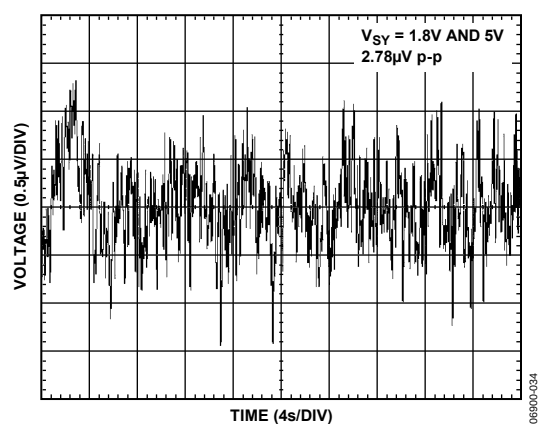


Figure 35. Voltage Noise 0.1 Hz to 10 Hz

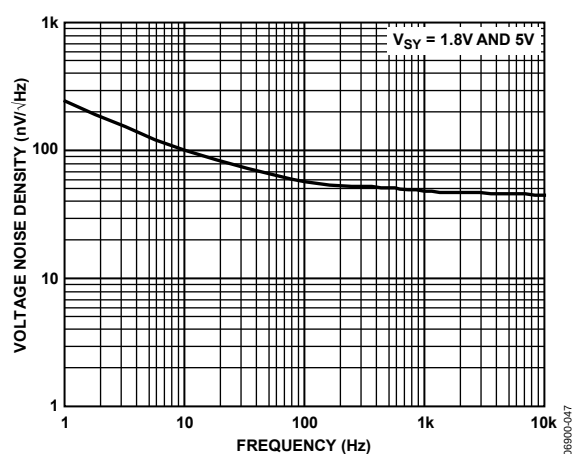


Figure 38. Voltage Noise Density vs. Frequency

AD8506/AD8508

T_A = 25°C, unless otherwise noted.

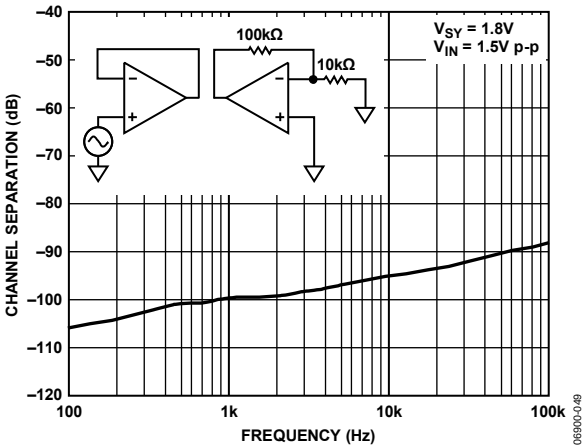


Figure 39. Channel Separation vs. Frequency

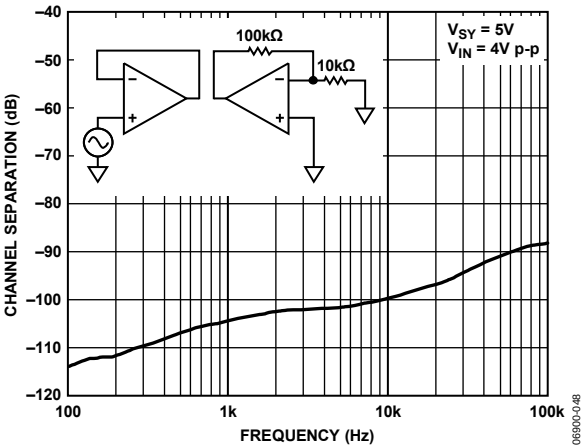


Figure 40. Channel Separation vs. Frequency

THEORY OF OPERATION

The AD8506/AD8508 are unity-gain stable CMOS rail-to-rail input/output operational amplifiers designed to optimize performance in current consumption, PSRR, CMRR, and zero crossover distortion, all embedded in a small package. The typical offset voltage is 500 μV , with a low peak-to-peak voltage noise of 2.8 μV p-p from 0.1 Hz to 10 Hz and a voltage noise density of 45 $\text{nV}/\sqrt{\text{Hz}}$ at 1 kHz.

The AD8506/AD8508 are designed to solve two key problems in low voltage battery-powered applications: battery voltage decrease over time and rail-to-rail input stage distortion.

In battery-powered applications, the supply voltage available to the IC is the voltage of the battery. Unfortunately, the voltage of a battery decreases as it discharges itself through the load. This voltage drop over the lifetime of the battery causes an error in the output of the op amps. Some applications requiring precision measurements during the entire lifetime of the battery use voltage regulators to power up the op amps as a solution. If a design uses standard battery cells, the op amps experience a supply voltage change from roughly 3.2 V to 1.8 V during the lifetime of the battery. This means that for a PSRR of 70 dB minimum in a typical op amp, the input-referred offset error is approximately 440 μV . If the same application uses the AD8506/AD8508 with a 100 dB minimum PSRR, the error is only 14 μV . It is possible to calibrate out this error or to use an external voltage regulator to power the op amp, but these solutions can increase system cost and complexity. The AD8506/AD8508 solve the impasse with no additional cost or error-nullifying circuitry.

The second problem with battery-powered applications is the distortion caused by the standard rail-to-rail input stage. Using a CMOS non-rail-to-rail input stage (that is, a single differential pair) limits the input voltage to approximately one V_{GS} (gate-source voltage) away from one of the supply lines. Because V_{GS} for normal operation is commonly over 1 V, a single differential pair input stage op amp greatly restricts the allowable input voltage range when using a low supply voltage. This limitation restricts the number of applications where the non-rail-to-rail input op amp was originally intended to be used. To solve this problem, a dual differential pair input stage is usually implemented (see Figure 41); however, this technique has its own drawbacks.

One differential pair amplifies the input signal when the common-mode voltage is on the high end, whereas the other pair amplifies the input signal when the common-mode voltage is on the low end. This method also requires a control circuitry to operate the two differential pairs appropriately. Unfortunately, this topology leads to a very noticeable and undesirable problem: if the signal level moves through the range where one input stage turns off and the other one turns on, noticeable distortion occurs (see Figure 42).

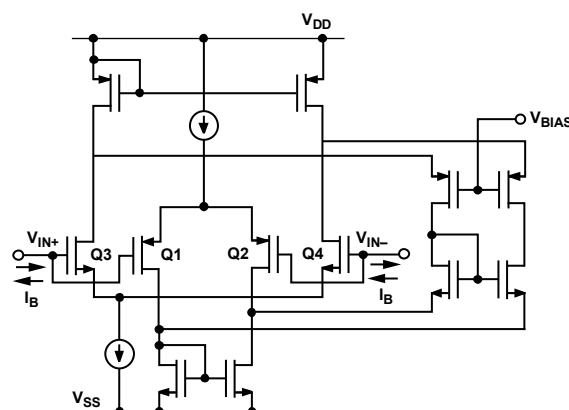


Figure 41. A Typical Dual Differential Pair Input Stage Op Amp (Dual PMOS Q1 and Q2 Transistors Form the Lower End of the Input Voltage Range Whereas Dual NMOS Q3 and Q4 Compose the Upper End)

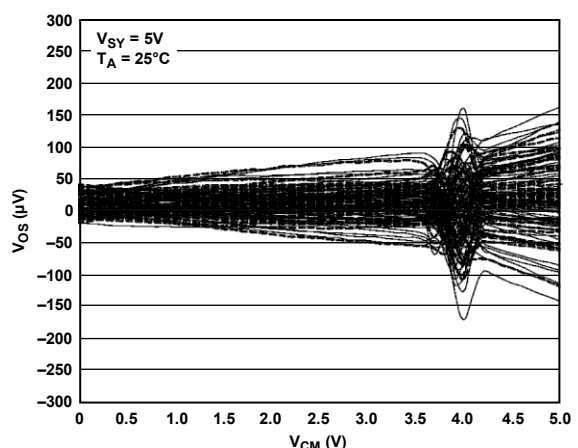


Figure 42. Typical Input Offset Voltage vs. Common-Mode Voltage Response in a Dual Differential Pair Input Stage Op Amp (Powered by 5 V Supply; Results of Approximately 100 Units per Graph Are Displayed)

This distortion forces the designer to come up with impractical ways to avoid the crossover distortion areas, therefore narrowing the common-mode dynamic range of the operational amplifier. The AD8506/AD8508 solve this crossover distortion problem by using an on-chip charge pump to power the input differential pair. The charge pump creates a supply voltage higher than the voltage of the battery, allowing the input stage to handle a wide range of input signal voltages without using a second differential pair. With this solution, the input voltage can vary from one supply extreme to the other with no distortion, thereby restoring the op amp full common-mode dynamic range.

The charge pump has been carefully designed so that switching noise components at any frequency, both within and beyond the amplifier bandwidth, are much lower than the thermal noise floor. Therefore, the spurious-free dynamic range (SFDR) is limited only by the input signal and the thermal or flicker noise. There is no intermodulation between input signal and switching noise.

Figure 43 displays a typical front-end section of an operational amplifier with an on-chip charge pump.

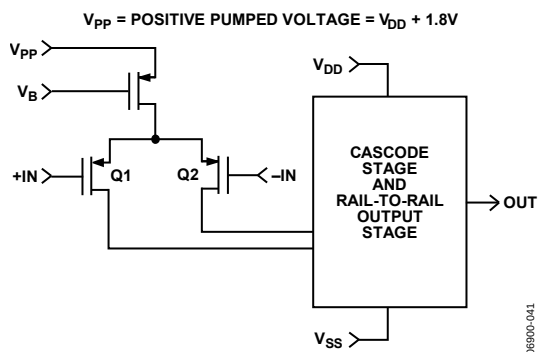


Figure 43. Typical Front-End Section of an Op Amp with Embedded Charge Pump

Figure 44, input offset voltage vs. input common-mode voltage response, shows the typical response of 12 devices from Figure 8. Figure 44 has been expanded so that it is easier to compare with Figure 42, typical input offset voltage vs. common-mode voltage response in a dual differential pair input stage op amp.

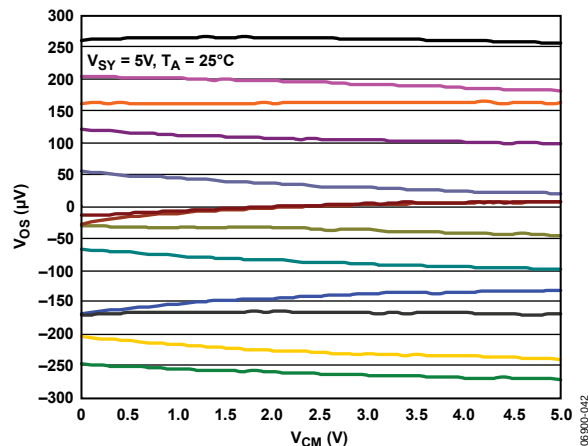
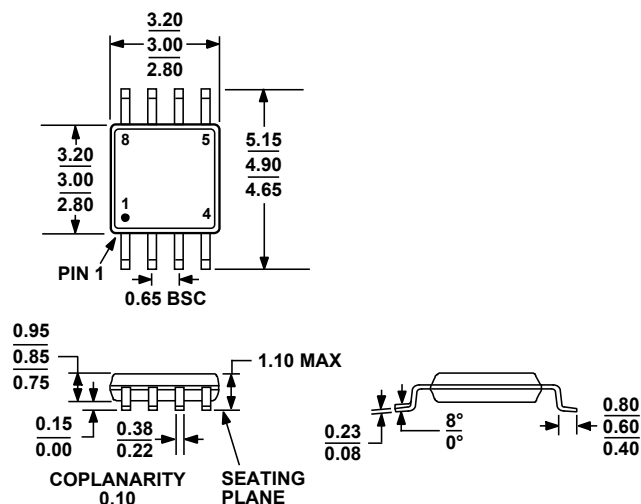


Figure 44. Input Offset Voltage vs. Input Common-Mode Voltage Response (Powered by a 5 V Supply; Results of 12 Units Are Displayed)

This solution improves the CMRR performance tremendously. For instance, if the input varies from rail-to-rail on a 2.5 V supply rail, using a part with a CMRR of 70 dB minimum, an input-referred error of 790 μ V is introduced. Another part with a CMRR of 52 dB minimum generates a 6.3 mV error. The AD8506/AD8508 CMRR of 90 dB minimum causes only a 79 μ V error. As with the PSRR error, there are complex ways to minimize this error, but the AD8506/AD8508 solve this problem without incurring unnecessary circuitry complexity or increased cost.

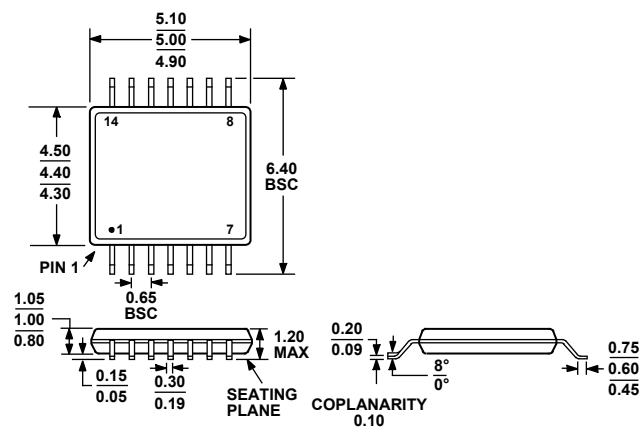
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-AA

Figure 47. 8-Lead Mini Small Outline Package [MSOP]
(RM-8)

Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-153-AB-1

Figure 48. 14-Lead Thin Shrink Small Outline Package [TSSOP]
(RU-14)

Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
AD8506ARMZ-R2 ¹	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A1X
AD8506ARMZ-REEL ¹	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A1X
AD8508ARUZ ¹	−40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14	
AD8508ARUZ-REEL ¹	−40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14	

¹ Z = RoHS Compliant Part.

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